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IRON ADMINISTRATION IN GALLIUM ARSENIDE

Ergash Yuldashevich Turaev*; Akmal Sattorov**

*Doctor of Physical and Mathematical Sciences,
Professor of Termez State University,
UZBEKISTAN
**Master's Student of Termez State University, UZBEKISTAN

ABSTRACT

Based on the data obtained by nuclear gamma-resonance spectroscopy, it is concluded that the state of impurity atoms depends both on the type of conductivity and on whether these atoms are in the surface layer or in the bulk of semiconductors.

KEYWORDS: *Iron, Nuclear Gamma-Resonance Spectroscopy, Impurity Atoms, Surface Layer, Bulk of Semiconductors.*

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